

NPN SILICON DUAL TRANSISTOR

Qualified per MIL-PRF-19500/495

Devices

2N5793

2N5794
2N5794U

Qualified Level

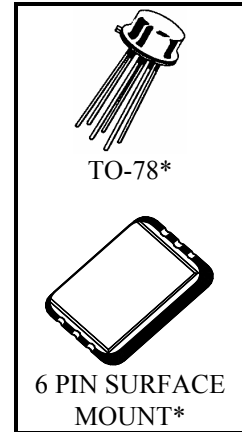
JAN
JANTX
JANTXV

MAXIMUM RATINGS

| Ratings | Symbol | Value | | Units |
|-------------------------------------------------------|-------------------|----------------------------|-----------------------------|--------------------|
| Collector-Emitter Voltage | V_{CEO} | 40 | | Vdc |
| Collector-Base Voltage | V_{CBO} | 75 | | Vdc |
| Emitter-Base Voltage | V_{EBO} | 6.0 | | Vdc |
| Collector Current | I_C | 600 | | mAdc |
| | | One Section ⁽¹⁾ | Total Device ⁽²⁾ | |
| Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$ | P_T | 0.5 | 0.6 | W |
| Operating & Storage Junction Temperature Range | T_{op}, T_{stg} | -65 to +200 | | $^{\circ}\text{C}$ |

1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$

2) Derate linearly 3.43 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$



*See MILPRF19500/495 for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

| Characteristics | Symbol | Min. | Max. | Unit |
|-----------------|--------|------|------|------|
|-----------------|--------|------|------|------|

OFF CHARACTERISTICS

| | | | | |
|-----------------------------------------------------------------------------------------|---------------|----|----------|-------------------------------------|
| Collector-Emitter Breakdown Current $I_C = 10 \text{ mAdc}$ | $V_{(BR)CEO}$ | 40 | | Vdc |
| Collector-Base Cutoff Current $V_{CB} = 75 \text{ Vdc}$ $V_{CB} = 50 \text{ Vdc}$ | I_{CBO} | | 10 10 | μAdc ηAdc |
| Emitter-Base Cutoff Current $V_{EB} = 6.0 \text{ Vdc}$ $V_{EB} = 4.0 \text{ Vdc}$ | I_{EBO} | | 10 10 | μAdc ηAdc |

